

# Si photodiodes

S1336 series

### **UV** to near IR for precision photometry

These Si photodiodes have sensitivity in the UV to near IR range. They are suitable for low-light-level detection in analysis and the like.

#### **Features**

- High sensitivity in UV range
- Low capacitance
- High reliability

#### - Applications

- Analytical instruments
- Optical measurement equipment

#### Structure / Absolute maximum ratings

Type no.				Absolute maximum ratings					
	Dimensional outline/ Window material*1	Package	Photosensitive area size	Reverse voltage VR max	Operating temperature Topr	Storage temperature Tstg			
			(mm)	(V)	(°C)	(°C)			
S1336-18BQ*2	(1)/Q	TO-18	1.1 × 1.1		-20 to +60	-55 to +80			
S1336-18BK	(2)/K	10-10	1.1 ^ 1.1		-40 to +100	-55 to +125			
S1336-5BQ*2	(3)/Q		2.4 × 2.4		-20 to +60	-55 to +80			
S1336-5BK	(4)/K	TO-5	2.4 ^ 2.4	5	-40 to +100	-55 to +125			
S1336-44BQ*2	(5)/Q	10-5	3.6 × 3.6	5	-20 to +60	-55 to +80			
S1336-44BK	(6)/K		3.0 \ 3.0		-40 to +100	-55 to +125			
S1336-8BQ*2	(7)/Q	TO-8	5.8 × 5.8		-20 to +60	-55 to +80			
S1336-8BK	(8)/K	10-6	3.0 \ 3.0		-40 to +100	-55 to +125			

<sup>\*1:</sup> Window material K=borosilicate glass, Q=quartz glass

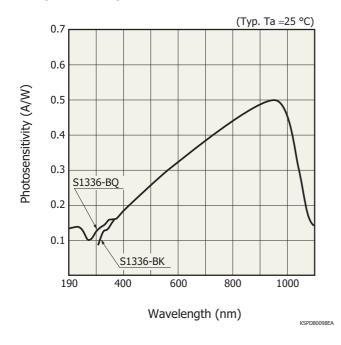
Note: Exceeding the absolute maximum ratings even momentarily may cause a drop in product quality. Always be sure to use the product within the absolute maximum ratings.

#### **■** Electrical and optical characteristics (Typ. Ta=25 °C, unless otherwise noted)

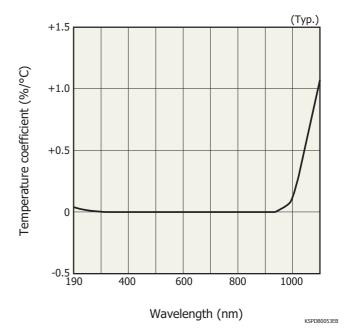
Type no.	Spectral response range	Peak sensitivity wavelength λp	Photosensitivity S (A/W)			Short circuit current Isc		Dark current ID VR=10 mV	coefficient of ID	VR=0 V	Terminal capacitance Ct	Rsh		Noise equivalent power	
			2	200	nm	He-Ne 100 lx		max.	TCID	RL=1 kΩ	f=10 kHz	VR=10 mV		NEP	
	(nm)	(nm)	λр	Min.	Тур.	633 nm	Min. (μΑ)	Typ. (µA)	(pA)	(times/°C)	(µs)	(pF)	Min. $(G\Omega)$	Typ. (GΩ)	(W/Hz <sup>1/2</sup> )
S1336-18BQ	190 to 1100	960	0.5	0.10	0.12	0.33	1	1.2	20	1.15	0.1	20	0.5	2	5.7 × 10 <sup>-15</sup>
S1336-18BK	320 to 1100			-	-		0.9	1.0	20						5.7 ~ 10
S1336-5BQ	190 to 1100			0.10	0.12		4	5	30		0.2	65	0.3	1	8.1 × 10 <sup>-15</sup>
S1336-5BK	320 to 1100			-	-										0.1 × 10
S1336-44BQ	190 to 1100			0.10	0.12		8	10	50		0.5	150	0.2	0.6	1.0 × 10 <sup>-14</sup>
S1336-44BK	320 to 1100			-	-										
S1336-8BQ	190 to 1100			0.10	0.12		22	28	100		1	380	0.1	0.4	1.3 × 10 <sup>-14</sup>
S1336-8BK	320 to 1100			-	-						1	360	0.1	0.4	1.5 × 10

<sup>\*2:</sup> Refer to "Precautions against UV light exposure."

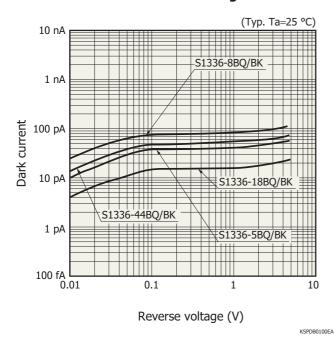
#### Spectral response



### **▶** Photosensitivity temperature characteristics



#### **Dark current vs. reverse voltage**

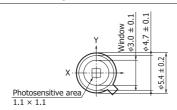


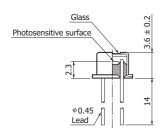
### Si photodiodes

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#### Dimensional outlines (unit: mm)

#### (1) S1336-18BQ





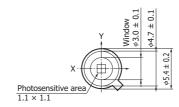


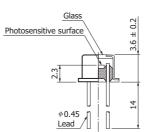


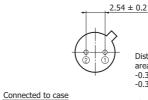
Distance from photosensitive area center to cap center  $-0.3 \le X \le +0.3$   $-0.3 \le Y \le +0.3$ 

KSPDA0197EB

#### (2) S1336-18BK







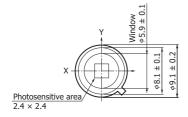
Distance from photosensitive area center to cap center  $-0.3 \le X \le +0.3$   $-0.3 \le Y \le +0.3$ 

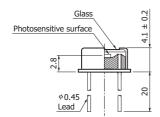
to case ② ⊶ ⊸ ①

The glass window may extend a maximum of 0.2 mm above the upper surface of the cap.

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#### (3) S1336-5BQ





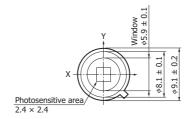


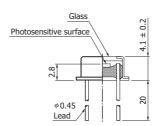


Distance from photosensitive area center to cap center  $-0.3 \le X \le +0.3$   $-0.3 \le Y \le +0.3$ 

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#### (4) S1336-5BK







Connected to case
② → ◄ → ①

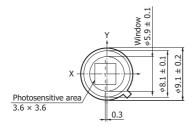
Distance from photosensitive area center to cap center  $-0.3 \le X \le +0.3$   $-0.3 \le Y \le +0.3$ 

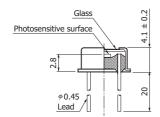
The glass window may extend a maximum of 0.2 mm above the upper surface of the cap.

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#### (5) S1336-44BQ



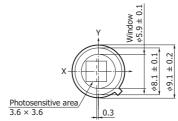


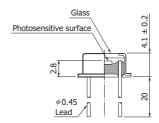


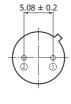
Connected to case **⊢** (1)

Distance from photosensitive area center to cap center  $-0.6 \le X \le 0$ -0.3≤Y≤+0.3

## (6) S1336-44BK





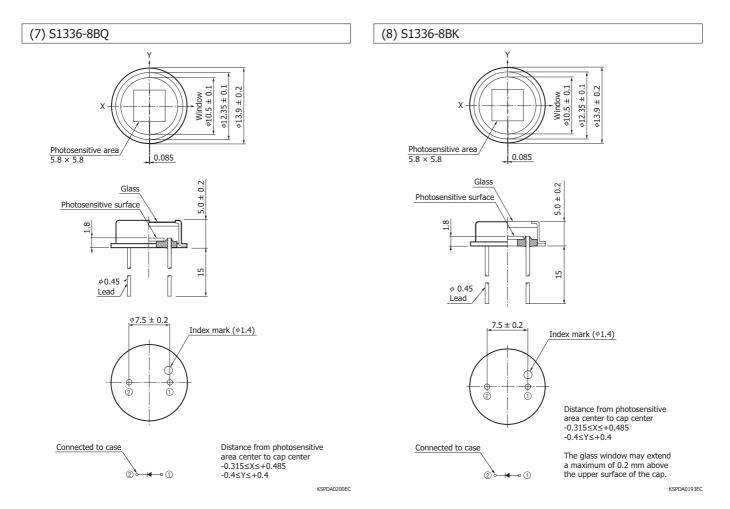


Distance from photosensitive area center to cap center -0.6≤X≤0 -0.3≤Y≤+0.3



The glass window may extend a maximum of 0.2 mm above the upper surface of the cap.

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#### Precautions against UV light exposure

- · When UV light irradiation is applied, the product characteristics may degrade. Such examples include degradation of the product's UV sensitivity and increase in dark current. This phenomenon varies depending on the irradiation level, irradiation intensity, usage time, and ambient environment and also varies depending on the product model. Before employing the product, we recommend that you check the tolerance under the ultraviolet light environment that the product will be used in.
- Exposure to UV light may cause the characteristics to degrade due to gas released from the resin bonding the product's component materials. As such, we recommend that you avoid applying UV light directly on the resin and apply it on only the inside of the photosensitive area by using an aperture or the like.

#### Si photodiodes

#### S1336 series

#### Related information

www.hamamatsu.com/sp/ssd/doc\_en.html

- Precautions
- · Disclaimer
- · Metal, ceramic, plastic package products
- Technical information
- · Si photodiode/Application circuit examples

Information described in this material is current as of October, 2015.

Product specifications are subject to change without prior notice due to improvements or other reasons. This document has been carefully prepared and the information contained is believed to be accurate. In rare cases, however, there may be inaccuracies such as text errors. Before using these products, always contact us for the delivery specification sheet to check the latest specifications.

The product warranty is valid for one year after delivery and is limited to product repair or replacement for defects discovered and reported to us within that one year period. However, even if within the warranty period we accept absolutely no liability for any loss caused by natural disasters or improper product use. Copying or reprinting the contents described in this material in whole or in part is prohibited without our prior permission.

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